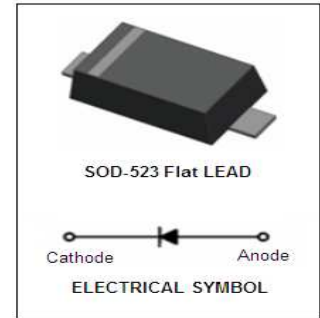


Features :

- Low Forward Voltage Drop;
- Guard Ring Construction for Transient Protection;
- Low Reverse Recover Time;
- Low Reverse Capacitance;

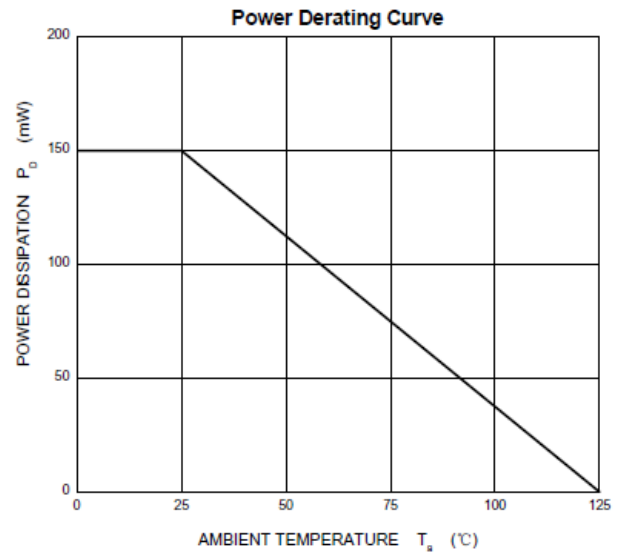
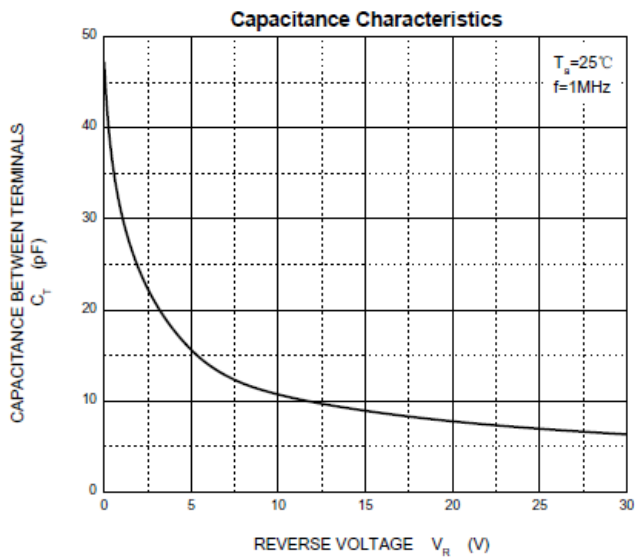
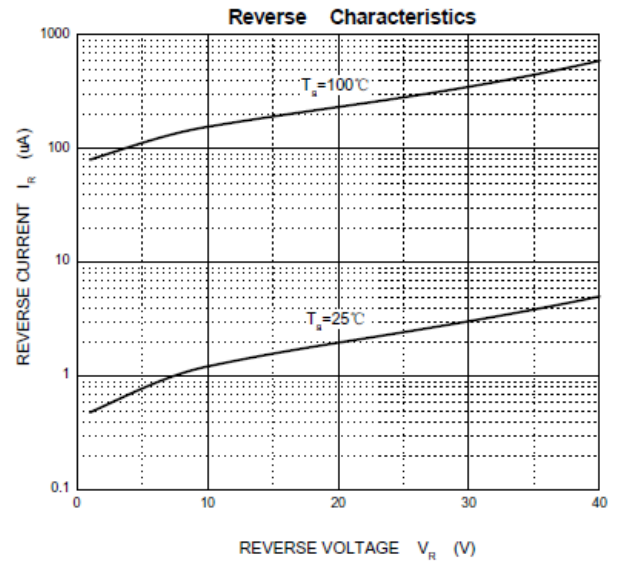
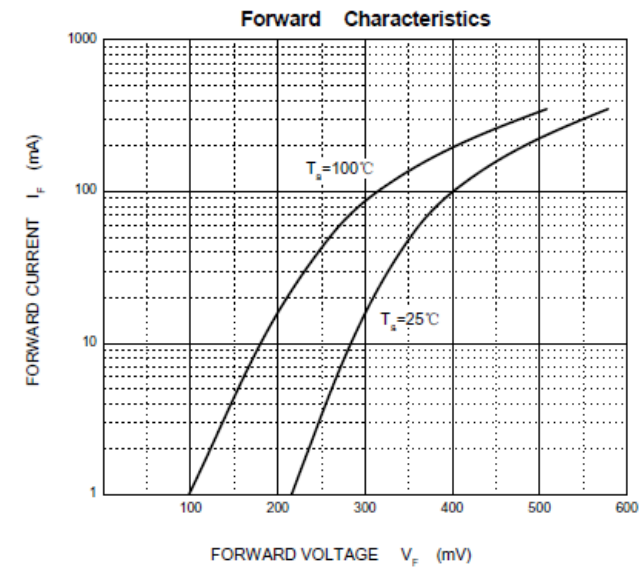
Marking: S4

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Peak Repetitive Peak Reverse Voltage	V_{RRM}	40	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	28	V
Forward Continuous current	I_O	350	mA
Repetitive Peak Forward Current @ $t \leq 1S$	I_{FRM}	1	A
Non- Repetitive Peak Forward Surge Current @ $t \leq 8.3mS$ Half Sine Wave	I_{FSM}	15	A
Power Dissipation	P_d	150	mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$	667	°C/mW
Junction Temperature	T_{stg}	125	°C
Storage Temperature	T_{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C)

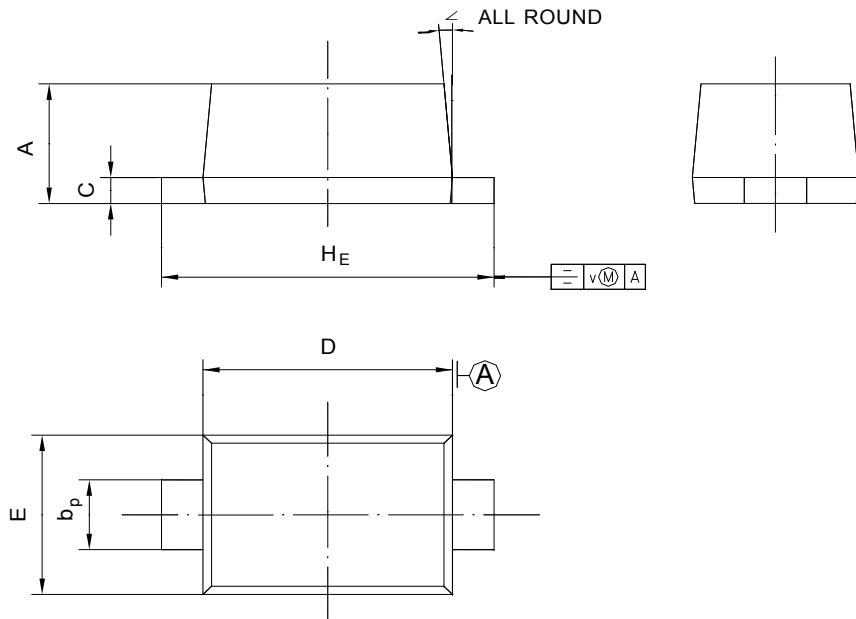
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_{(BR)}$	$I_R=100 \mu A$	40			V
Reverse current	I_R	$V_R=30V$			5	μA
		$V_R=20V$			2	
		$V_R=30V$			5	
Forward Voltage	V_F	$I_F=1mA$		0.27		V
		$I_F=5mA$		0.32		
		$I_F=20mA$			0.37	
		$I_F=200mA$			0.55	
Diode Capacitance	C_D	$V_R=4V, f=1.0MHz$		50		pF
Recover Reverse Time	t_{rr}	$I_F=I_R=200mA, I_{rr}=0.1 \times I_R, R_L=100 \Omega$		10		nS

典型特性曲线图



PACKAGE OUTLINE

Plastic surface mounted package; 2 leads



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.70 0.60	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°